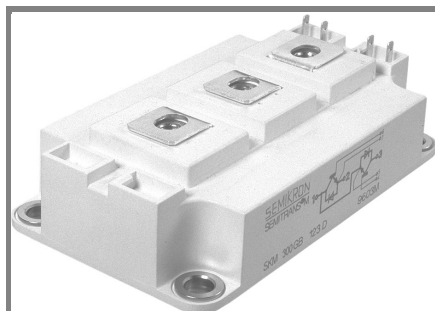


SKM 400GB125D



SEMITRANS™ 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

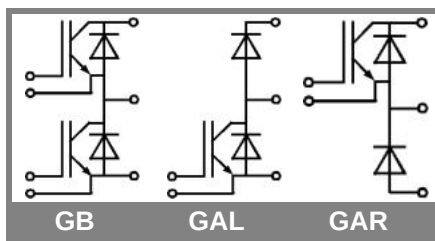
SKM 400GAR125D

Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications

- Switched mode power supplies at $f_{sw} > 20\text{kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$



Absolute Maximum Ratings		$T_c = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25\text{ (80) °C}$	400 (300)	A
I_{CRM}	$t_p = 1\text{ ms}$	600	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	4000	V

Inverse diode			
I_F	$T_c = 25\text{ (80) °C}$	390 (260)	A
I_{FRM}	$t_p = 1\text{ ms}$	600	A
I_{FSM}	$t_p = 10\text{ ms; sin.; } T_j = 150\text{ °C}$	2900	A

Freewheeling diode			
I_F	$T_c = 25\text{ (80) °C}$	390 (260)	A
I_{FRM}	$t_p = 1\text{ ms}$	600	A
I_{FSM}	$t_p = 10\text{ ms; sin.; } T_j = 150\text{ °C}$	2900	A

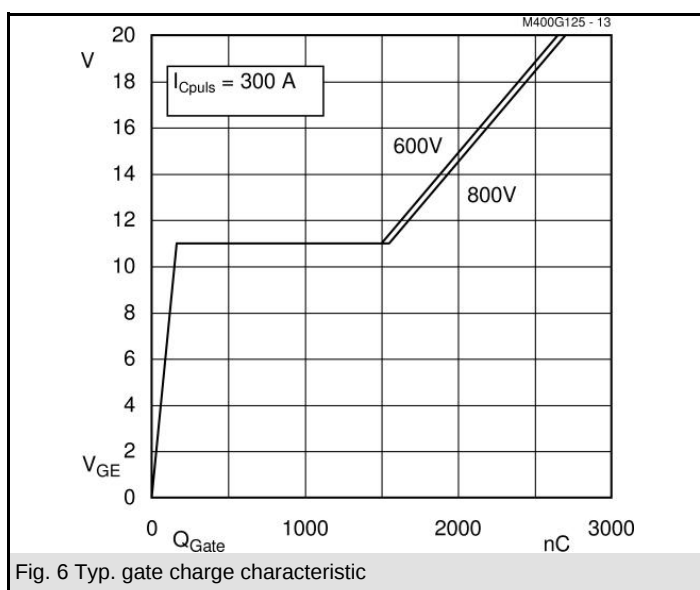
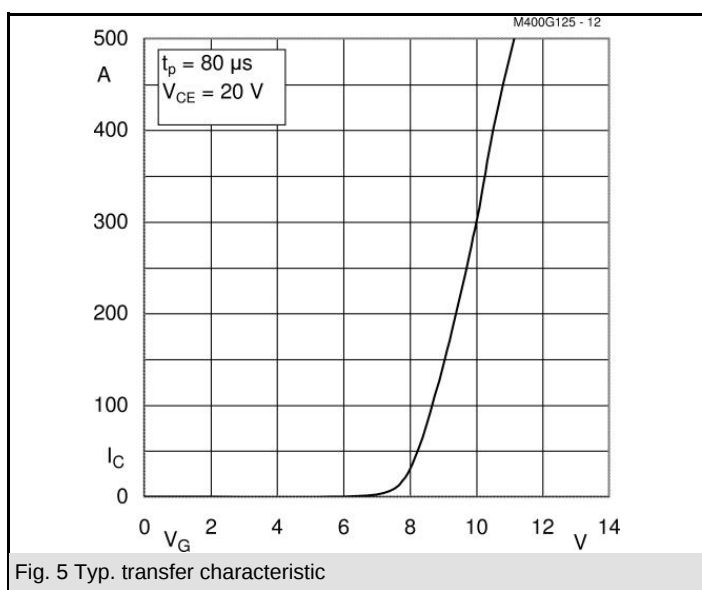
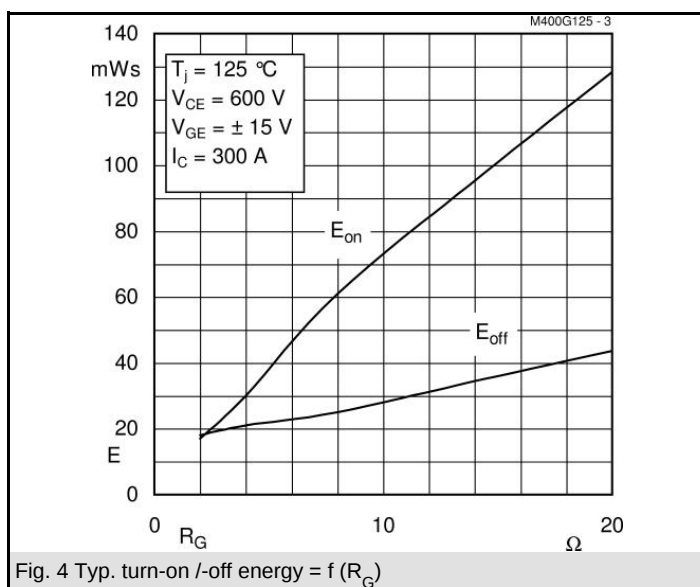
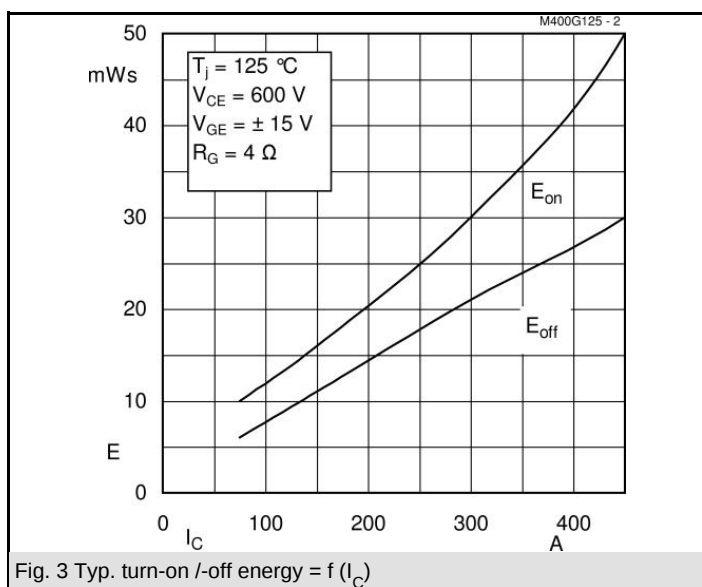
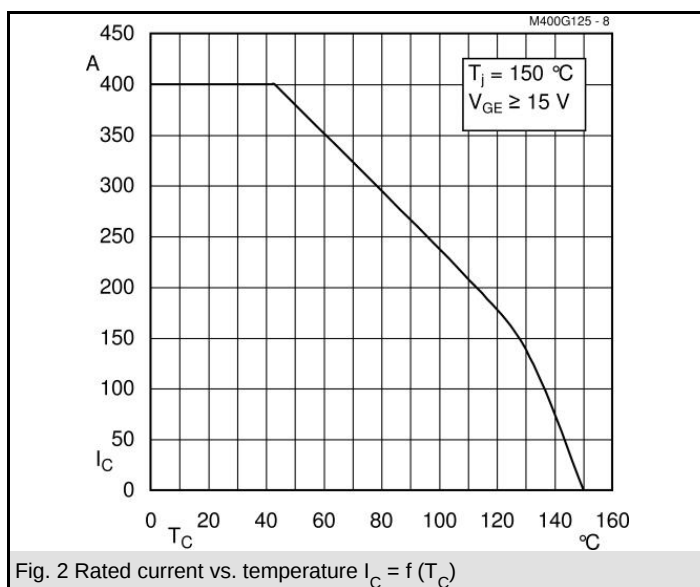
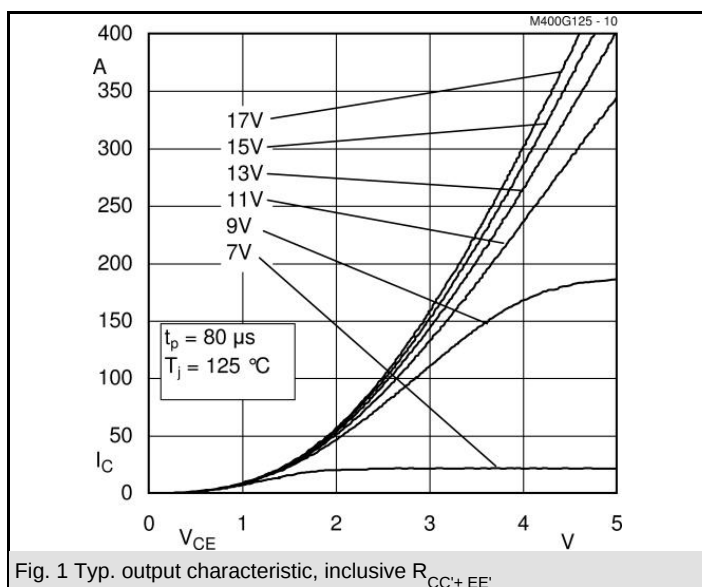
Characteristics		$T_c = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 12\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25\text{ (125) °C}$		0,15	0,45	mA
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1,4 (1,7)		V
r_{CE}	$V_{GE} = 15\text{ V}, T_j = 25\text{ (125) °C}$				mΩ
$V_{CE(sat)}$	$I_{Cnom} = 300\text{ A}, V_{GE} = 15\text{ V}$, chip level		3,3	3,85	V
C_{ies}	under following conditions		22	30	nF
C_{oes}	$V_{GE} = 0, V_{CE} = 25\text{ V}, f = 1\text{ MHz}$		3,3	4	nF
C_{res}			1,2	1,6	nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c = 25\text{ (125) °C}$		0,35 (0,5)		mΩ
$t_{d(on)}$	$V_{CC} = 600\text{ V}, I_{Cnom} = 300\text{ A}$		70		ns
t_r	$R_{Gon} = R_{Goff} = 2\text{ Ω}, T_j = 125\text{ °C}$		50		ns
$t_{d(off)}$	$V_{GE} = \pm 15\text{ V}$		500		ns
t_f			32		ns
$E_{on} (E_{off})$			17 (18)		mJ

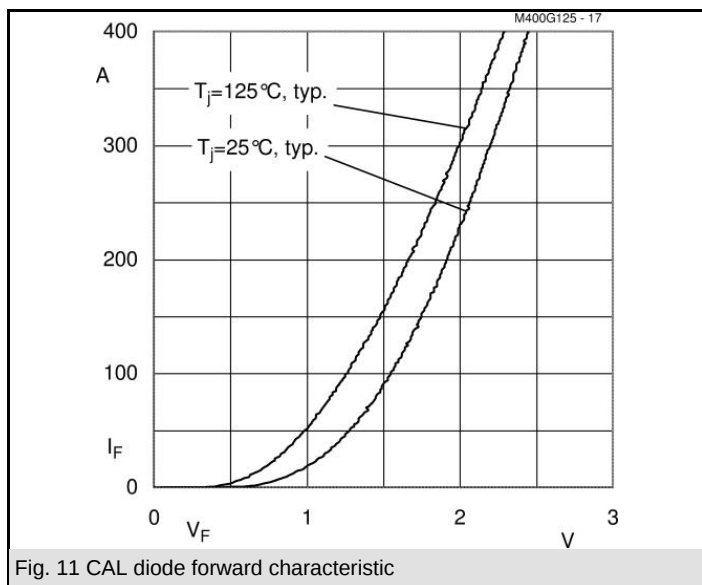
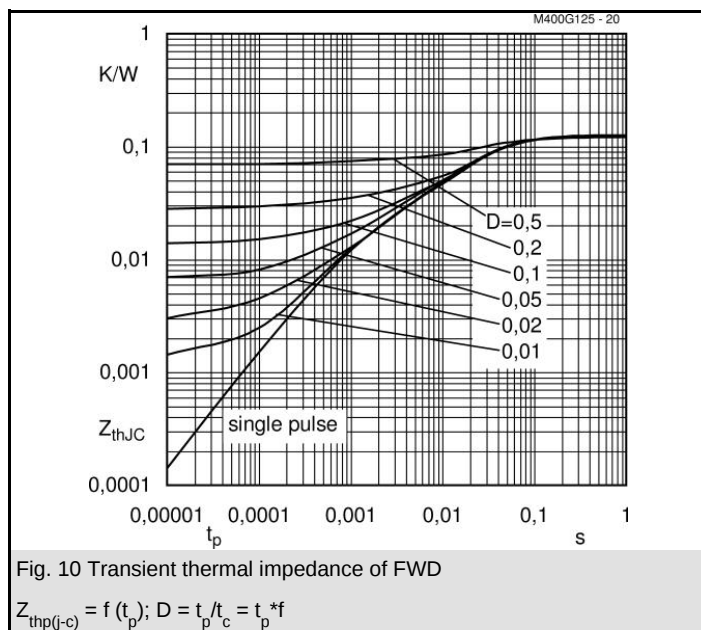
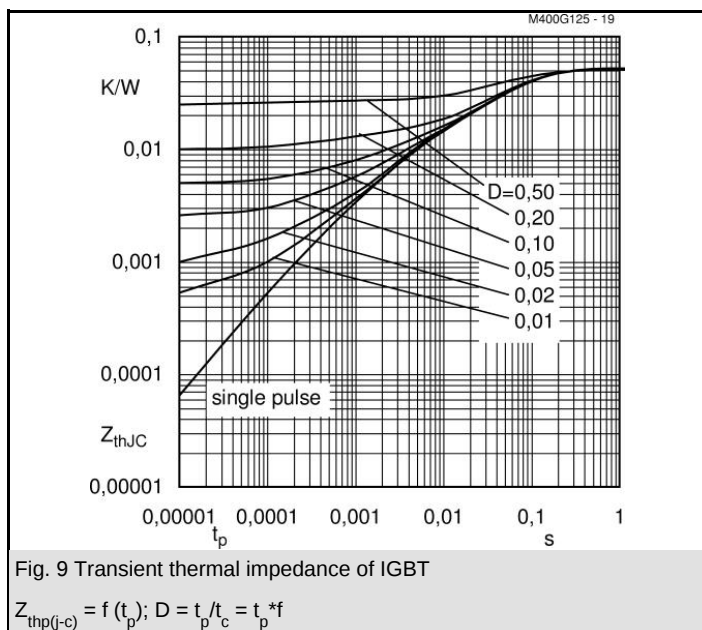
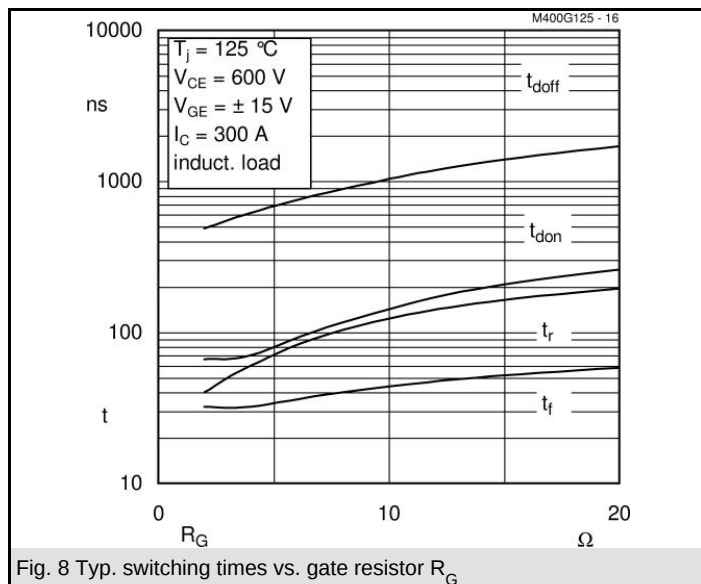
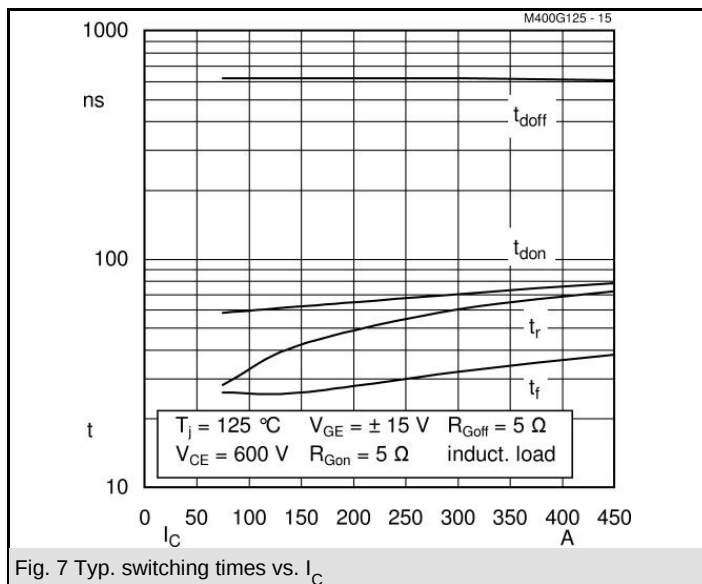
Inverse diode			
$V_F = V_{EC}$	$I_{Fnom} = 300\text{ A}; V_{GE} = 0\text{ V}; T_j = 25\text{ (125) °C}$	2 (1,8)	2,5
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$	1,1	1,2
r_T	$T_j = 25\text{ (125) °C}$	3	3,3
I_{RRM}	$I_{Fnom} = 300\text{ A}; T_j = 125\text{ () °C}$	85 (140)	A
Q_{rr}	$di/dt = A/\mu s$	13 (40)	μC
E_{rr}	$V_{GE} = 0\text{ V}$		mJ

FWD			
$V_F = V_{EC}$	$I_F = 300\text{ A}; V_{GE} = 0\text{ V}, T_j = 25\text{ (125) °C}$	2 (1,8)	2,5
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		
r_T	$T_j = 25\text{ (125) °C}$		
I_{RRM}	$I_F = 300\text{ A}; T_j = 125\text{ () °C}$		
Q_{rr}	$di/dt = A/\mu s$		
E_{rr}	$V_{GE} = 0\text{ V}$		

Thermal characteristics			
$R_{th(j-c)}$	per IGBT	0,05	K/W
$R_{th(j-c)D}$	per Inverse Diode	0,125	K/W
$R_{th(j-c)FD}$	per FWD	0,125	K/W
$R_{th(c-s)}$	per module	0,038	K/W

Mechanical data			
M_s	to heatsink M6	3	Nm
M_t	to terminals M6	2,5	Nm
w			325 g

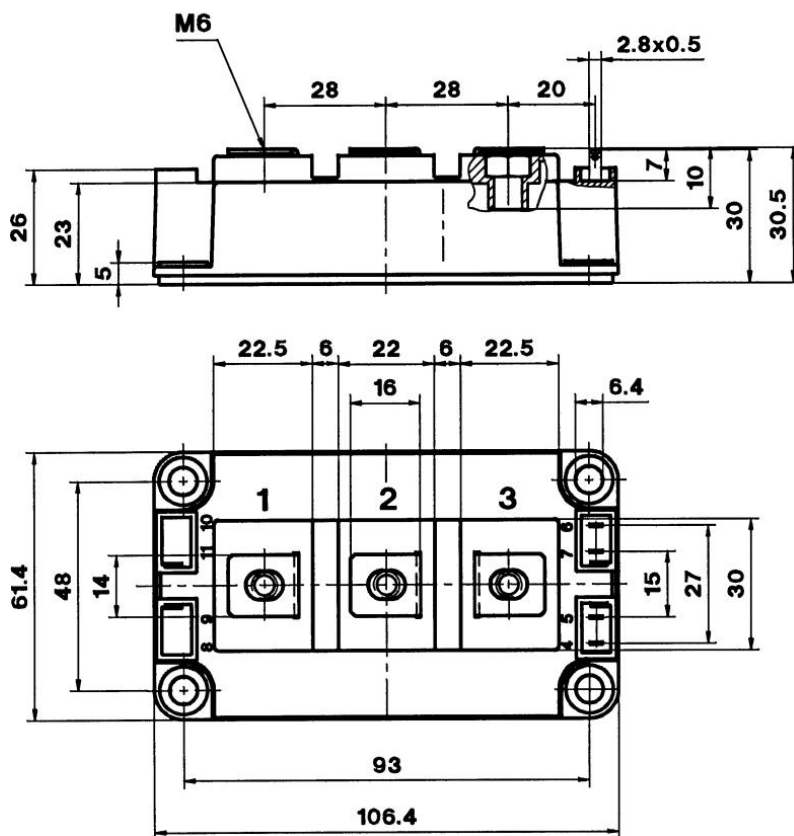




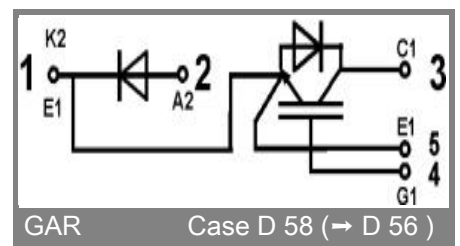
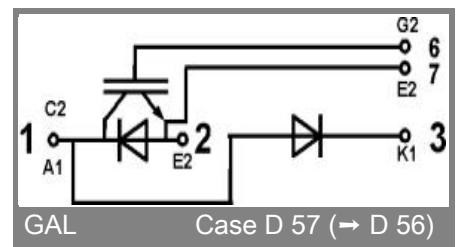
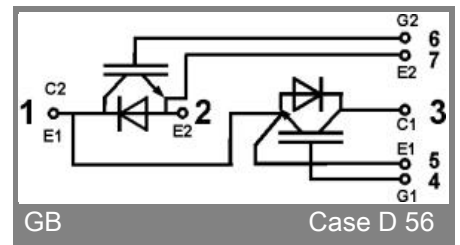
UL Recognized
File no. E 63 532

Dimensions in mm

CASED56



Case D 56



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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